NSN 5961-01-084-0815

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-084-0815 **Inclosure Material:** Glass **Overall Length:** Between 0.140 inches and 0.195 inches **Terminal Length:** Between 0.900 inches and 1.300 inches **Overall Diameter:** Between 0.135 inches and 0.185 inches **Mounting Method:** Terminal **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 42.6 working peak reverse voltage, peak total value **Current Rating Per Characteristic:** 18.60 amperes source cutoff current universal **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector megahertz **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Special Features:** 1500w maximum reverse peak pulse power; 80.7v maximum clamping voltage **Precious Material And Location:**

Terminal surface option silver

Precious Material:

Silver

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

2 uninsulated wire lead

Specification Data:

81349-mil-s-19500/516 government specification

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

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